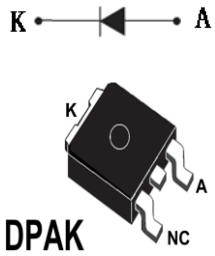
FP8K60AA

主要参数 MAIN CHARACTERISTICS

$I_{F(AV)}$	8A
V_{RRM}	600 V
$V_{F(typ)}$ 150℃	1.5V
$T_{rr(typ)}$	12ns

封装 **Package**



用途

- 有源功率校正电路
- 开关电源
- PFC

APPLICATIONS

- Active power factor correction
- Switch power supply
- PFC

产品特性

- 低功耗，高效率
- 高可靠性
- 环保（RoHS）产品

FEATURES

- Low power loss, high efficiency
- High reliability
- RoHS product

订货信息 ORDER MESSAGE

订 货 型 号 Order codes		印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen Free-Tube		
FP8K60AA-R-A	FP8K60AA-R-AR	FP8K60AA	DPAK

绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项　目 Parameter	符　号 Symbol	数　值 Value	单　位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}	600	V
平均正向整流电流　T_C=110℃ Average Forward Rectified Curren	$I_{F(AV)}$	8	A
非重复浪涌正向电流 Non-Repetitive Surge Forward Current　t=10ms	I_{FSM}	70	A
结温 Junction Temperature	T_j	175	℃
储存温度 Storage temperature range	T_{STG}	-65~+175	℃

电特性 ELECTRICAL CHARACTERISTICS (Tc=25℃ unless otherwise specified)

项　目 Parameter	测试条件 Tests conditions		最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单位 Unit
V_R	I_R =50μA		600	-	-	V
I_R	T_j =25℃	$V_R=V_{RRM}$	-	0.012	1	μA
	T_j =150℃		-	5.5	100	μA
V_F	T_j =25℃	I_F=8A	-	2.6	3.2	V
	T_j =150℃		-	1.5	1.9	V
Cj	V_R = 200V F=1MHz		-	15	-	pF
trr	I_F=0.5A, I_R=1A, I_{RR}=0.25A		-	12	18	ns
trr	I_F=1A, V_R=30V, di_F/dt=-200A/μs		-	12	18	ns
trr	I_F=8A, V_R=200V, di_F/dt=-200A/μs Tc =25℃		-	18	-	ns
Qrr			-	17	-	nc
I_{RRM}			-	1.6	-	A
trr	I_F=8A, V_R=200V, di_F/dt=-200A/μs Tc =125℃		-	38	-	ns
Qrr			-	90	-	nc
I_{RRM}			-	4.4	-	A

热特性 THERMAL CHARACTERISTICS

项　　目 Parameter	符　号 Symbol	封　装 Package	最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单　位 Unit
结到管壳的热阻 Thermal Resistance Junction to Case	$R_{th(j-c)}$	DPAK	-	-	3	℃/W
结到环境的热阻 Thermal Resistance Junction to Ambient	$R_{th(j-a)}$	DPAK	-	50	-	℃/W

特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Fig.1 TYPICAL FORWARD CHARACTERISTICS

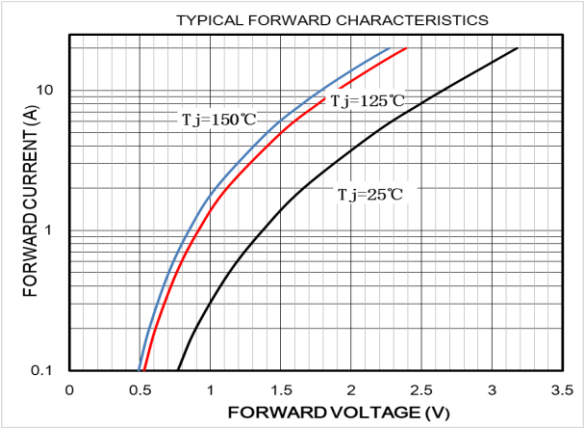


Fig.2 TYPICAL REVERSE CHARACTERISTICS

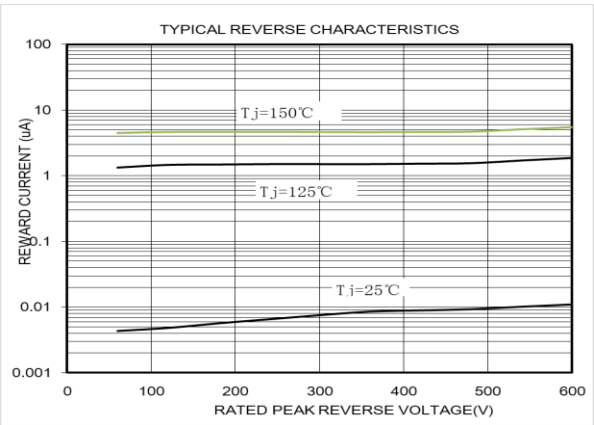


Fig.3 TYPCAL JUNCTION CAPACITANCE

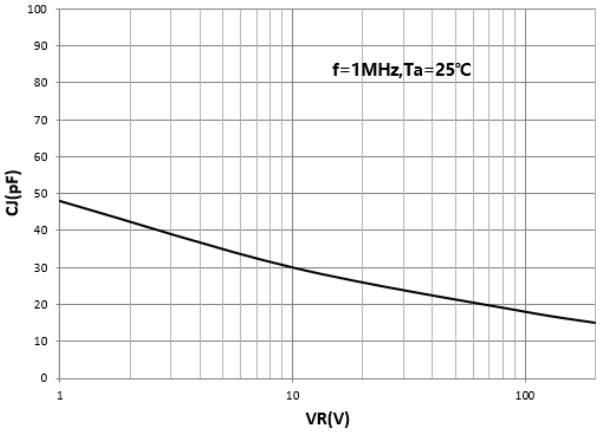


Fig.4 Reverse recovery time versus dIF/dt

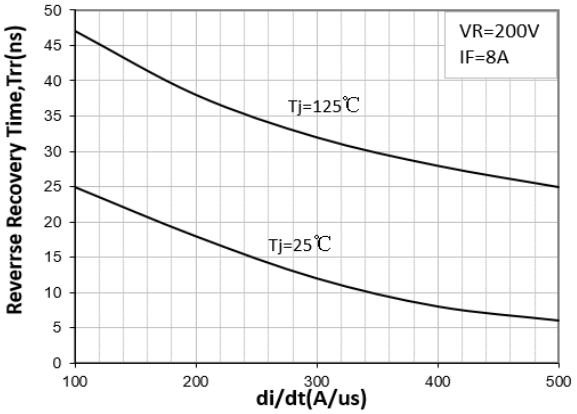


Fig.5 Reverse recovery charges versus dIF/dt

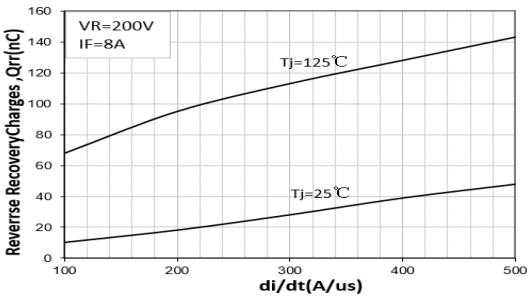
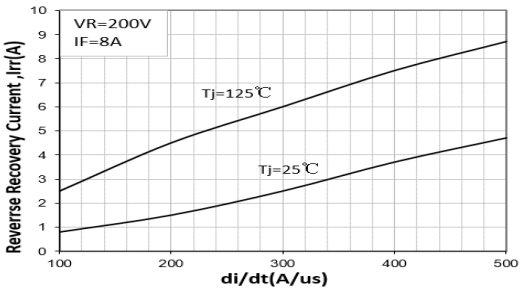


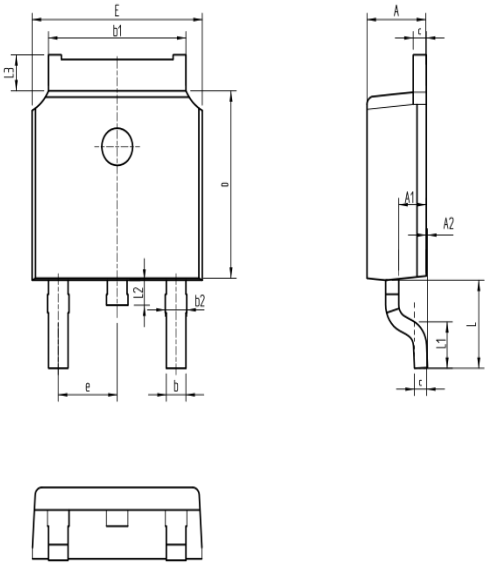
Fig.6 Peak reverse recovery current versus dIF/dt



外形尺寸 PACKAGE MECHANICAL DATA

DPAK

单位 Unit ： mm



SYMBOL	mm	
	MIN	MAX
A	2.16	2.41
A1	0.97	1.17
A2	0.00	0.15
b	0.63	0.93
b1	5.13	5.53
b2	0.66	0.96
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
e	2.286BSC	
L	2.50	3.30
L1	1.20	1.80
L2	0.60	1.00
L3	0.85	1.30

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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
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